

Fig. 1

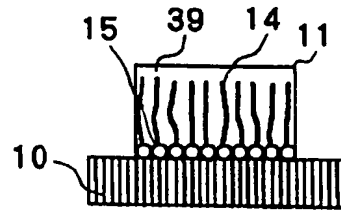


Fig. 2

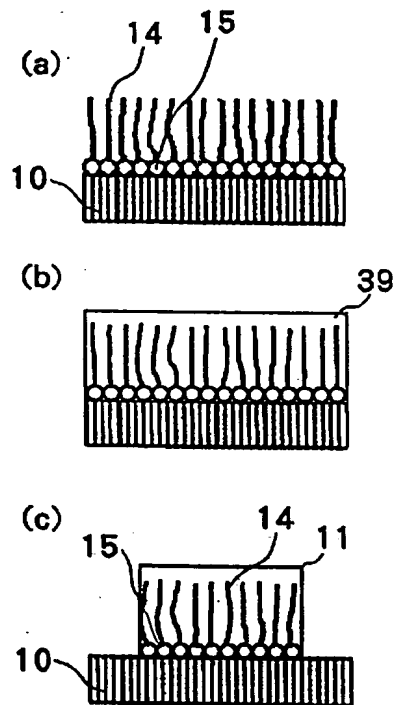


Fig. 3

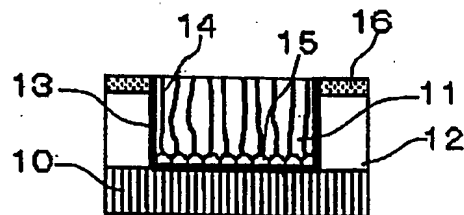


Fig. 4

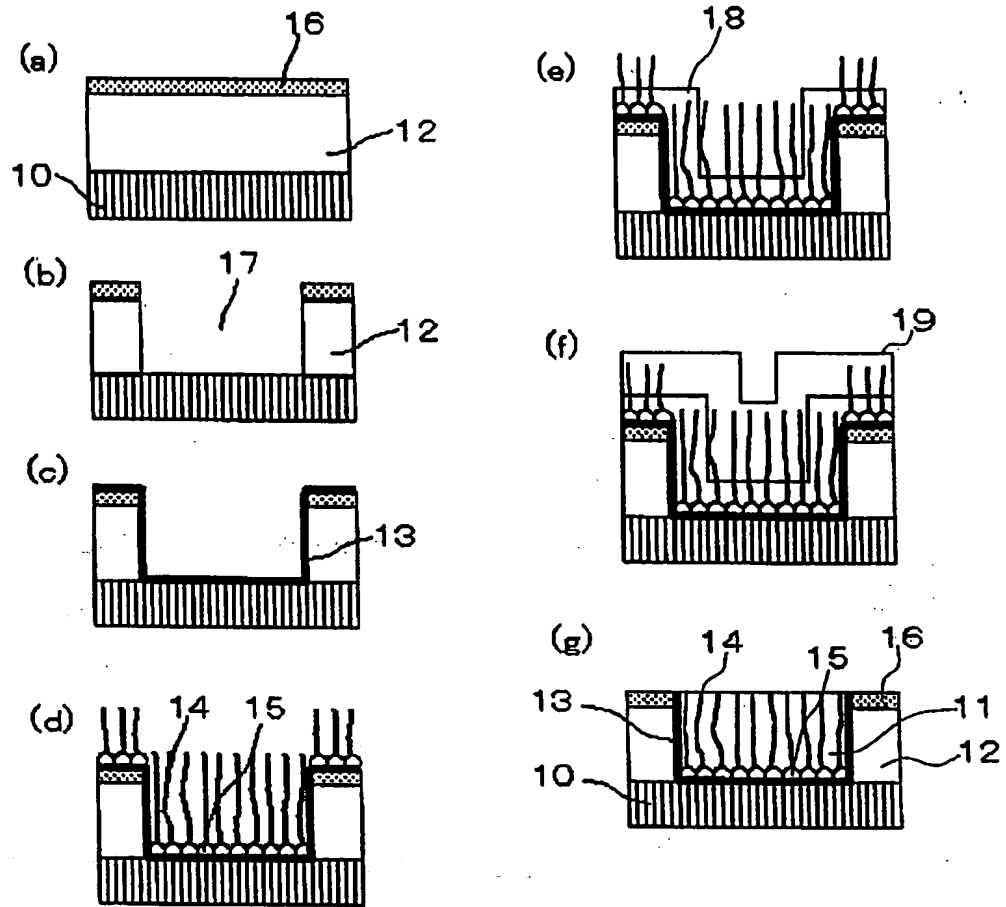


Fig. 5

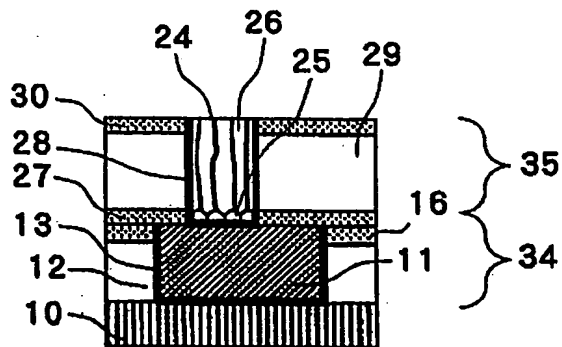


Figure 1 consists of seven cross-sectional views of a semiconductor device, labeled (a) through (g), illustrating the sequential steps of its fabrication:

- (a)** Shows a substrate 10 with a central region 11. A layer 12 is formed over the substrate, and a layer 13 is formed on top of layer 12. A layer 16 is formed on top of layer 13. A layer 27 is formed on top of layer 16. A layer 29 is formed on top of layer 27. A layer 30 is formed on top of layer 29.
- (b)** Shows the removal of the top layers 27, 29, and 30, leaving a recessed area 31.
- (c)** Shows the removal of the top layers 27, 29, and 30, leaving a recessed area 28.
- (d)** Shows the removal of the top layers 27, 29, and 30, leaving a recessed area 24 and 25.
- (e)** Shows the removal of the top layers 27, 29, and 30, leaving a recessed area 32.
- (f)** Shows the removal of the top layers 27, 29, and 30, leaving a recessed area 33.
- (g)** Shows the final device structure. The substrate 10 is covered by a layer 11. A layer 12 is formed over the substrate. A layer 13 is formed on top of layer 12. A layer 16 is formed on top of layer 13. A layer 24 is formed on top of layer 16. A layer 25 is formed on top of layer 24. A layer 26 is formed on top of layer 25. A layer 27 is formed on top of layer 26. A layer 28 is formed on top of layer 27. A layer 29 is formed on top of layer 28. A layer 30 is formed on top of layer 29. The top layers 24, 25, 26, 27, 28, and 29 are collectively labeled 35. The bottom layers 10, 11, 12, 13, and 16 are collectively labeled 34.

Fig. 7

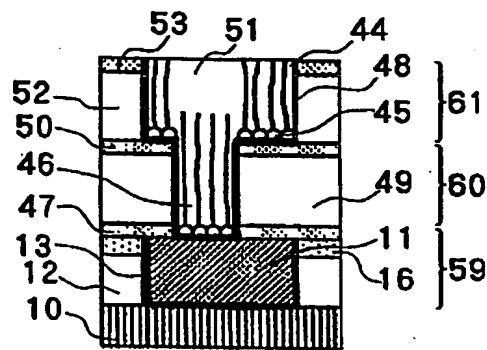


Fig. 8

